B

Half-bridge SCR configuration integrated

In a single package

High-thermal-conductivity DBC insulation 0 g 0 0 7(o)-G [(c)-17(o)-12(n)-12(d)-12(uc)-4(t)-6n-US

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(@ T_C = 25℃ unless otherwise specified)

		B	E			D
			□	C □	□	
Peak forward voltage	I_T=210A, t_P=380	V_T			1.80	V
Repetitive peak off-state current	V_D = V_{DRM},T_{vj} = 25	I_{DRM}			100	A
	V_D = V_{DRM},T_{vj} = 125				30	mA
Reverse leakage current	V_R = V_{RRM},T_{vj} = 25	I_{RRM}			100	A
	V_R = V_{RRM},T_{vj} = 125				30	mA
Threshold voltage	For power loss calculation only T_{vj} = 125	V_{TO}			0.92	V
Dynamic resistance	T_{vj} = 125					

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